

Thyristor Module

V_{RRM} = 2x 1600 V

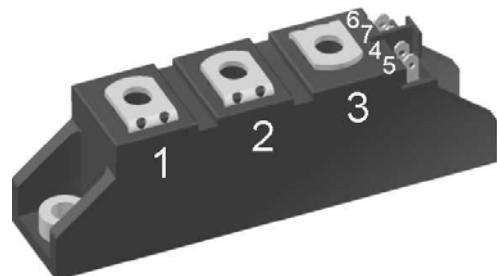
I_{TAV} = 35 A

V_T = 1.22 V

Phase leg

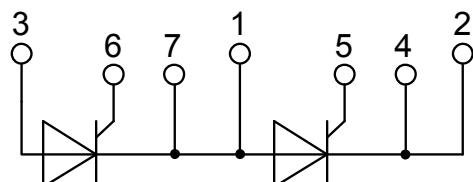
Part number

MCMA35P1600TA



Backside: isolated

E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

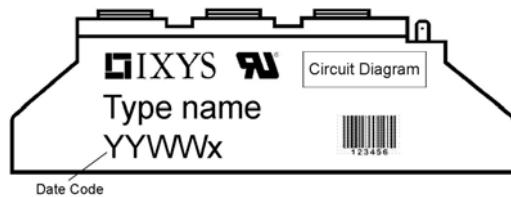
- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Thyristor			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ C$			1700	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ C$			1600	V
I_{RD}	reverse current, drain current	$V_{RD} = 1600 V$ $V_{RD} = 1600 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 140^\circ C$		100 6	μA mA
V_T	forward voltage drop	$I_T = 35 A$ $I_T = 70 A$ $I_T = 35 A$ $I_T = 70 A$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		1.23 1.50 1.22 1.56	V V V V
I_{TAV}	average forward current	$T_C = 85^\circ C$	$T_{VJ} = 140^\circ C$		35	A
$I_{T(RMS)}$	RMS forward current	180° sine			55	A
V_{TO} r_T	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 140^\circ C$		0.87 9.8	V $m\Omega$
R_{thJC}	thermal resistance junction to case				0.9	K/W
R_{thCH}	thermal resistance case to heatsink			0.20		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		120	W
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$ $V_R = 0 V$ $T_{VJ} = 140^\circ C$ $V_R = 0 V$		520 560 440 475	A A
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$ $V_R = 0 V$ $T_{VJ} = 140^\circ C$ $V_R = 0 V$		1.35 1.31 970 940	kA ² s kA ² s A ² s A ² s
C_J	junction capacitance	$V_R = 400 V$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$	22		pF
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$ $t_p = 300 \mu s$	$T_C = 140^\circ C$		10 5 0.5	W W W
P_{GAV}	average gate power dissipation					
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^\circ C; f = 50 \text{ Hz}$ repetitive, $I_T = 105 A$ $t_p = 200 \mu s; di_G/dt = 0.45 A/\mu s;$ $I_G = 0.45 A; V_D = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 35 A$			150	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	$T_{VJ} = 140^\circ C$		1000	V/ μs
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$		1.5 1.6	V V
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$		78 200	mA mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^\circ C$		0.2	V
I_{GD}	gate non-trigger current				5	mA
I_L	latching current	$t_p = 10 \mu s$ $I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$	$T_{VJ} = 25^\circ C$		450	mA
I_H	holding current	$V_D = 6 V$ $R_{GK} = \infty$	$T_{VJ} = 25^\circ C$		200	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$	$T_{VJ} = 25^\circ C$		2	μs
t_q	turn-off time	$V_R = 100 V; I_T = 35 A; V_D = \frac{2}{3} V_{DRM}$ $T_{VJ} = 140^\circ C$ $di/dt = 10 A/\mu s; dv/dt = 20 V/\mu s; t_p = 200 \mu s$		185		μs

Package TO-240AA			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			80	A
T_{VJ}	virtual junction temperature		-40		140	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				90		g
M_D	mounting torque		2.5		4	Nm
M_T	terminal torque		2.5		4	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	13.0	9.7		mm
$d_{Spb/Abp}$		terminal to backside	16.0	16.0		mm
V_{ISOL}	isolation voltage	$t = 1$ second $t = 1$ minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA		4800 4000	V V



Part number

M = Module
 C = Thyristor (SCR)
 M = Thyristor
 A = (up to 1800V)
 35 = Current Rating [A]
 P = Phase leg
 1600 = Reverse Voltage [V]
 TA = TO-240AA-1B

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCMA35P1600TA	MCMA35P1600TA	Box	6	512944

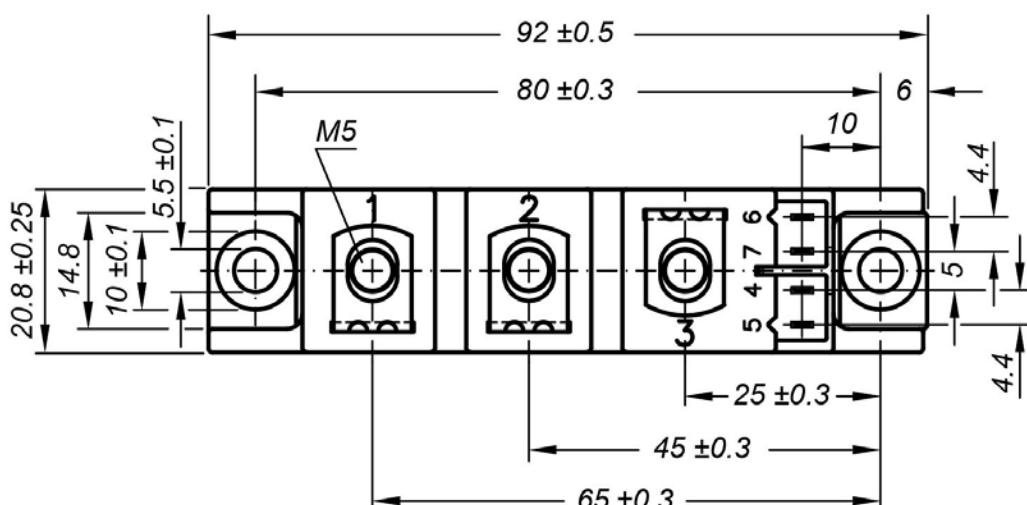
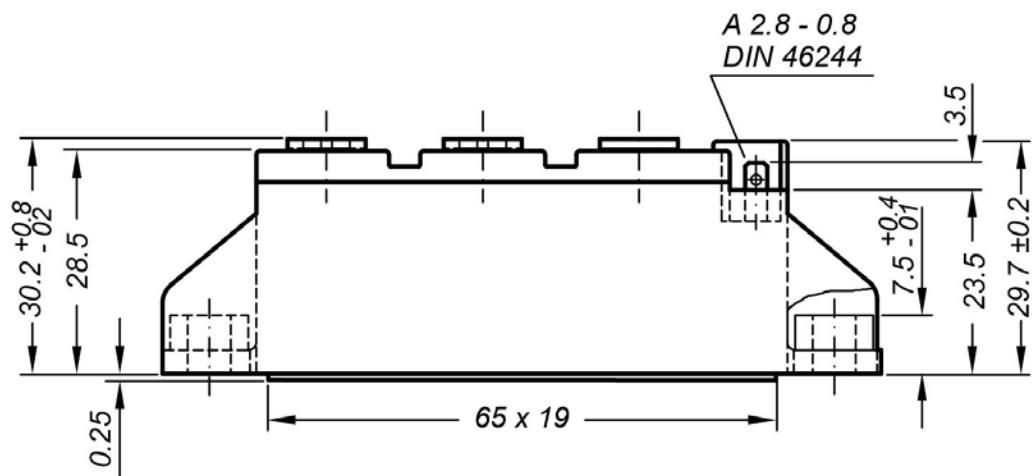
Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 140$ °C

	V_0	R_0	Thyristor	
$V_{0\max}$	threshold voltage	0.87		V
$R_{0\max}$	slope resistance *	8.6		mΩ

Outlines TO-240AA



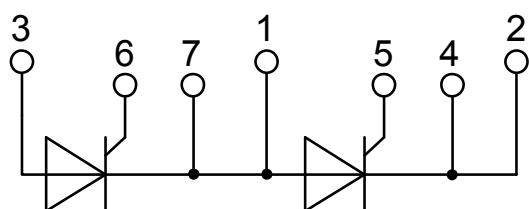
Optional accessories: Keyed gate/cathode twin plugs

Wire length: 350 mm, gate = white, cathode = red

UL 758, style 3751

Type ZY 200L (L = Left for pin pair 4/5)

Type ZY 200R (R = Right for pin pair 6/7)



Thyristor

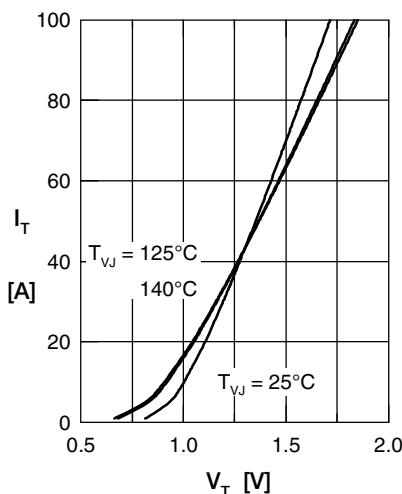


Fig. 1 Forward characteristics

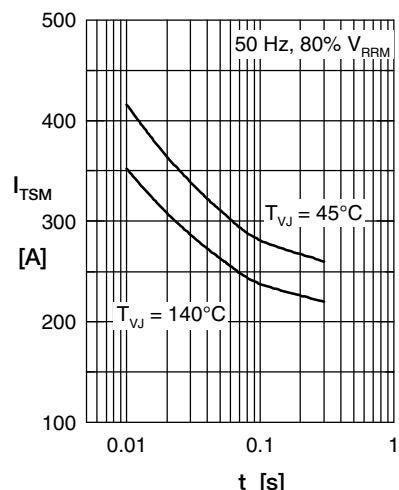
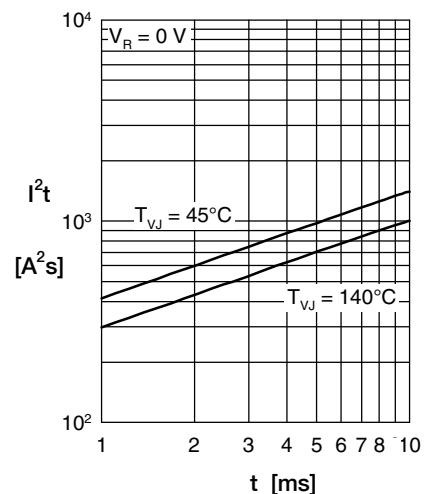
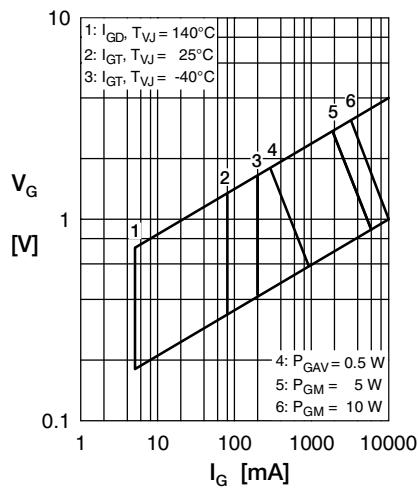
Fig. 2 Surge overload current
 I_{TSM} : crest value, t : durationFig. 3 I^2t versus time (1-10 s)

Fig. 4 Gate voltage & gate current

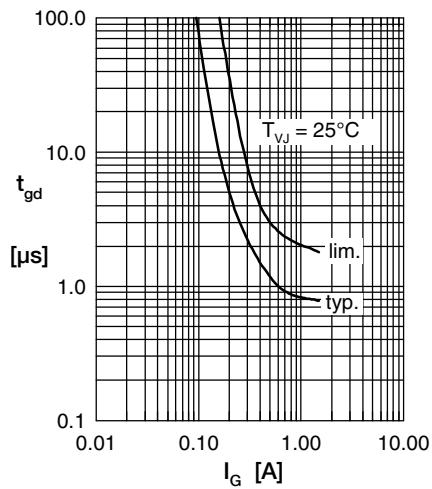
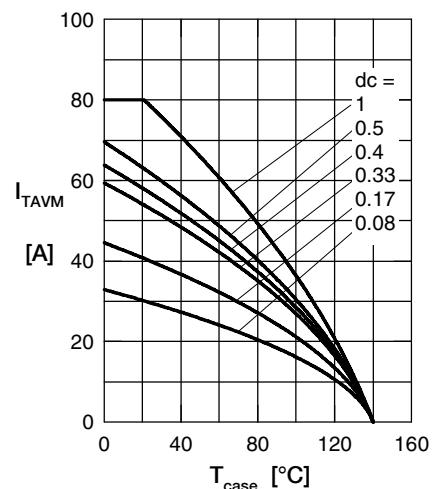
Fig. 5 Gate controlled delay time t_{gd} 

Fig. 6 Max. forward current at case temperature

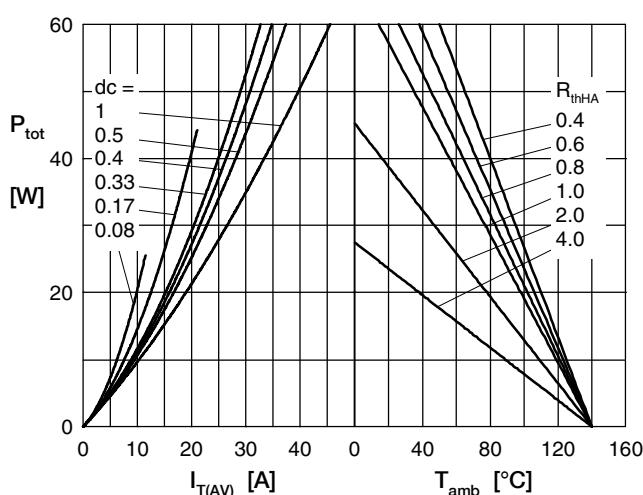
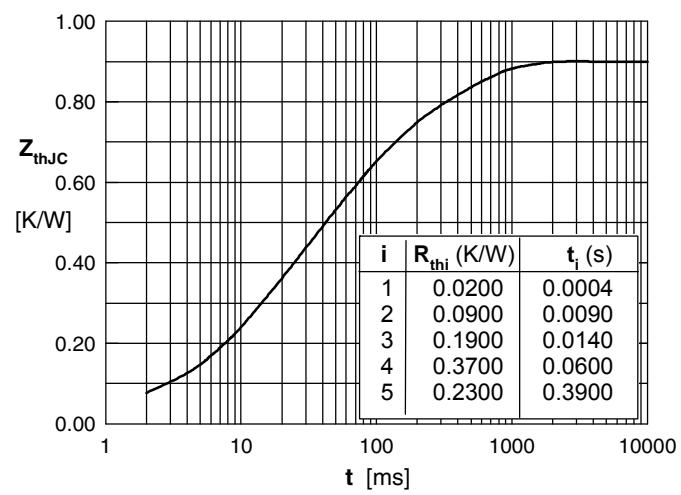
Fig. 7a Power dissipation versus direct output current
Fig. 7b and ambient temperature

Fig. 8 Transient thermal impedance junction to case